RELEASE Ø DATA SHEET





### **GRF5529**

# HIGH EFFICIENCY POWER AMPLIFIER 2.9 to 3 GHz

#### **FEATURES**

- Flexible Biasing Voltage and Current
- 5 V Supply Voltage
- Digital Shutdown
- High Ruggedness
- Process: InGaP HBT
- -40 to 85 °C Operating Temperature Range
- Compact 3 x 3 mm QFN-16 Package

#### Reference: 5 V / 110 mA I<sub>CCQ</sub> / 2.95 GHz

• Gain: 29.5 dB

• P<sub>SAT</sub>: 34 dBm CW Mode, PAE: 57%

• Evaluation Board Noise Figure: 3.4 dB

#### **APPLICATIONS**

- Civilian Radar
- Military Radar
- Radio Location
- Repeaters/Boosters

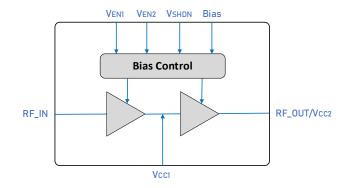
#### **DESCRIPTION**

The GRF5529 is a high-efficiency power amplifier designed for saturated applications at 2.95 GHz. It is capable of 34 dBm saturated output power when in CW mode and is ideal for pulsed operation.

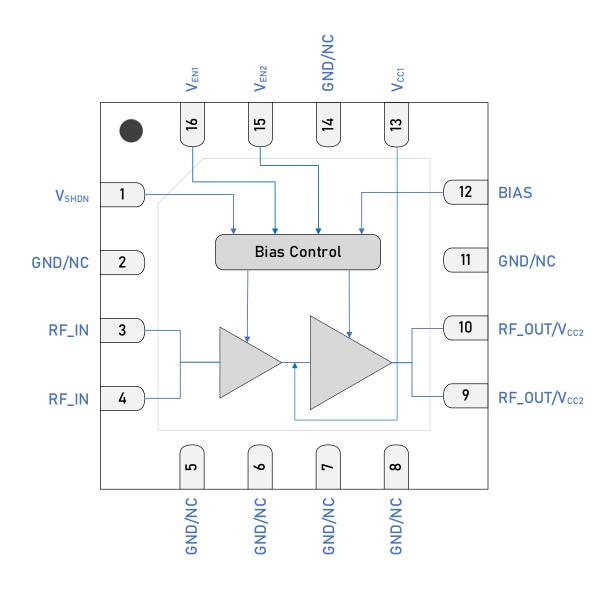
Please consult with the GRF applications engineering team for custom tuning/evaluation board data.

Additional tunes can be found on the GRF5529 "Custom Tunes" product page: GRF5529 Custom Tunes

#### **BLOCK DIAGRAM**







3 x 3 mm QFN-16 Pin Out (Top View)



### **GRF5529** High Efficiency Power Amplifier 2.95 GHz

### **Pin Assignments**

Pin	Name	Description	Note
1	Vshdn	Digital Shutdown Pin	V <sub>SHDN</sub> ≥ 1.5 V disables device. V <sub>SHDN</sub> ≤ 0.2 V enables device.
2, 5, 6, 7, 8, 11, 14	GND/NC	Ground or No Connect	No internal connection to die. These pins can be left unconnected, or be connected to ground (recommended). Use a via as close to the pin as possible if grounded.
3, 4	RF_IN	RF Input	Pins 3 & 4 tied together on system board. An external DC blocking capacitor must be used.
9, 10	RF_OUT/V <sub>CC2</sub>	PA Output/Bias Voltage	Pins 9 & 10 tied together on system board. $V_{\text{CC2}}$ must be applied to this pin via an RF choke.
12	Bias	Bias Circuit Supply	Connect to V <sub>CC2</sub> through external resistor.
13	V <sub>CC1</sub>	Bias Voltage	Connect to V <sub>CC1</sub> through external resistor.
15	$V_{EN2}$	Enable2 Voltage Input	$V_{EN2}$ and series resistor set $I_{CCQ}$ for the output stage. $V_{EN2} \le 0.2$ volts disables stage 2.
16	V <sub>EN1</sub>	Enable1 Voltage Input	$V_{EN1}$ and series resistor set $I_{CCQ}$ for the input stage. $V_{EN1} \le 0.2$ volts disables stage 1. Connecting an external decoupling capacitor to ground is required for optimal NF performance.
PKG BASE	GND	Ground	Provides DC and RF ground for the LNA, as well as thermal heat sink. Recommend multiple 8 mil vias beneath the package for optimal RF and thermal performance. Refer to evaluation board top layer graphic on schematic page.



### **Absolute Ratings**

Parameter	Symbol	Min.	Max.	Unit
Supply Voltage	V <sub>CC</sub>		5.5	V
Maximum Average RF Input Power: Load VSWR: 2.0:1, all phase angles, T <sub>PKG BASE</sub> = 25°C	PIN MAX		10	dBm
Maximum Average RF Input Power: Load VSWR: 1.5:1, all phase angles, T <sub>PKG BASE</sub> = -40°C	P <sub>IN MAX</sub>		10	dBm
Operating Temperature (package base)	Tpkg base	-40	85	°C
Maximum Junction Temperature (MTTF > 10 <sup>6</sup> Hours)	Тл мах		170	°C
Maximum Dissipated Power Stage 1: DC only (no RF applied).	P <sub>DISS MAX</sub>		500	mW
Maximum Dissipated Power Stage 2: DC only (no RF applied).	P <sub>DISS MAX</sub>		850	mW

#### **Electrostatic Discharge**

Charged Device Model	CDM	1000	V
Human Body Model	НВМ	1500	V

#### Storage

Storage Temperature	T <sub>STG</sub>	-65	150	°C
Moisture Sensitivity Level	MSL		1	



### **Caution! ESD Sensitive Device.**

**Exceeding Absolute Maximum Rating conditions may cause permanent damage.** 

Note: For additional information, please refer to *Manufacturing Note MN-001* — *Package and Manufacturing Information*.



All Guerrilla RF products are provided in RoHS compliant lead (Pb)-free packaging requiring no exemptions. Additional information for this topic can be found at this link - *Environmental and Restricted Substance Statement Library* 





### **Recommended Operating Conditions**

		Specification				
Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
Supply Voltage	Vcc	3	5	5.5	V	
Operating Temperature (package base)	TPKG BASE	-40		85	°C	
RF Frequency Range	F <sub>RF</sub>	2.9		3	GHz	Typical application schematic using the 2.95 GHz tuning set (notes 1 & 2).
RF_IN Port Impedance	Z <sub>RFIN</sub>		50		Ω	Single-ended.
RF_OUT Port Impedance	Zrfout		50		Ω	Single-ended.

**Note 1:** Operation outside of this range is supported by using different custom tunes. Examples of other optimized tunes can be found here: <u>GRF5529</u> <u>Custom Tunes</u>

Note 2: Contact the Guerrilla RF Applications team for guidance on optimizing the tuning of the device for alternative bands.





### **Nominal Operating Parameters – General**

The following conditions apply unless noted otherwise: typical application schematic using the 2.95 GHz tune,  $V_{CC} = 5 \text{ V}$ ,  $I_{CCQ} = 110 \text{ mA}$ ,  $F_{TEST} = 2.95 \text{ GHz}$ ,  $M5 = 6.65 \text{ k}\Omega$ ,  $M9 = 4.75 \text{ k}\Omega$ ,  $50 \Omega$  system impedance,  $T_{PKG BASE} = 25 ^{\circ}C$ . Evaluation board losses are included within the specifications.

		Specification				
Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
Supply Quiescent Current	Iccq	80	110	150	mA	Iccq1 + Iccq2 (no RF applied).
Enable Current 1	I <sub>ENABLE1</sub>		0.5		mA	
Enable Current 2	I <sub>ENABLE2</sub>		0.83		mA	
Operating Temperature Range	T <sub>PKG</sub> BASE	-40		85	°C	Measured on package base.
Switching Rise Time	T <sub>RISE</sub>		40		ns	Disabled mode to Gain mode (note 3).
Switching Fall Time	T <sub>FALL</sub>		8		ns	Gain mode to Disabled mode (note 4).

#### **Disabled Mode**

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#### **Thermal Data**

Thermal Resistance: (IR Scan Method)	Θις		38		°C/W	On standard evaluation board (note 5).
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**Note 3:** Switching Time: 50% of  $V_{ENABLE}$  to 90% of  $P_{OUT}$ . **Note 4:** Switching Time: 50% of  $V_{ENABLE}$  to 10% of  $P_{OUT}$ . **Note 5:** MTTF > 106 hours for  $T_{CHANNEL} \le 170$  °C.





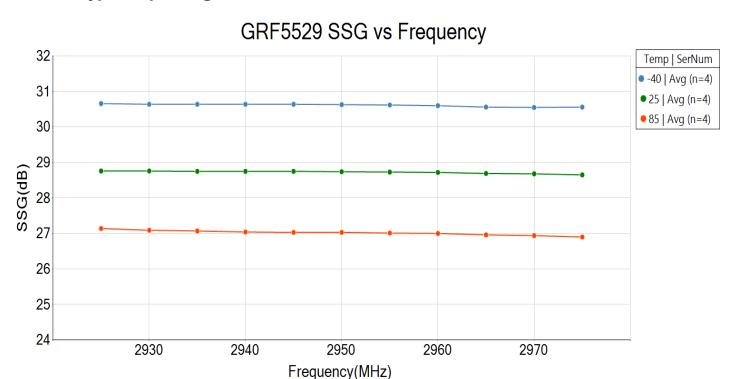
### Nominal Operating Parameters – RF: 2.95 GHz, 5 V Operation

The following conditions apply unless noted otherwise: typical application schematic using the 2.95 GHz tune,  $V_{CC} = 5$  V,  $I_{CCQ} = 110$  mA,  $F_{TEST} = 2.95$  GHz, M5 = 6.65 k $\Omega$ , M9 = 4.75 k $\Omega$  50  $\Omega$  system impedance,  $T_{PKG \ BASE} = 25$  °C. Evaluation board losses are included within the specifications.

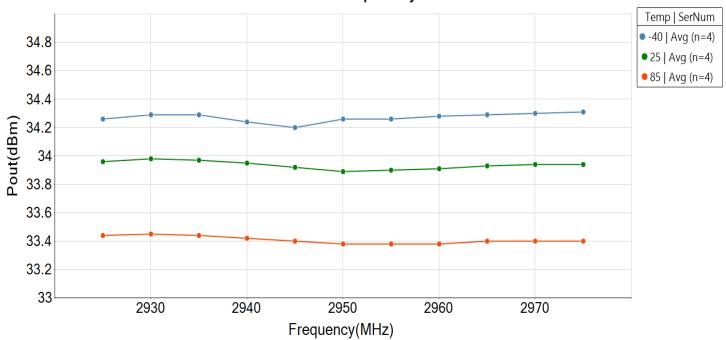
			Specification			
Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
Small Signal Gain	S21	27.5	29.5		dB	
Input Return Loss	S11		< -20		dB	
Output Return Loss	S22		< -6		dB	
Reverse Isolation	S12		< -38		dB	
Noise Figure	NF		3.4		dB	On standard evaluation board.
Saturated Output Power	P <sub>SAT</sub>		34		dBm	RF input power: 8 dBm CW.
Power Added Efficiency	PAE		57		%	RF input power: 8 dBm CW.



### **GRF5529 Typical Operating Curves: 2.95 GHz Tune**

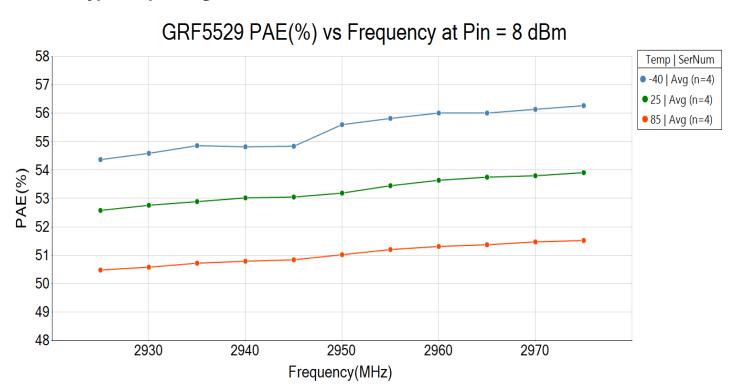


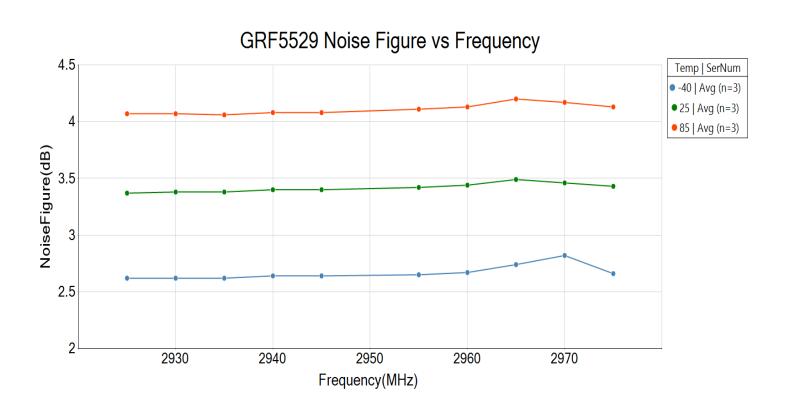
## GRF5529 Pout vs Frequency at Pin = 8 dBm





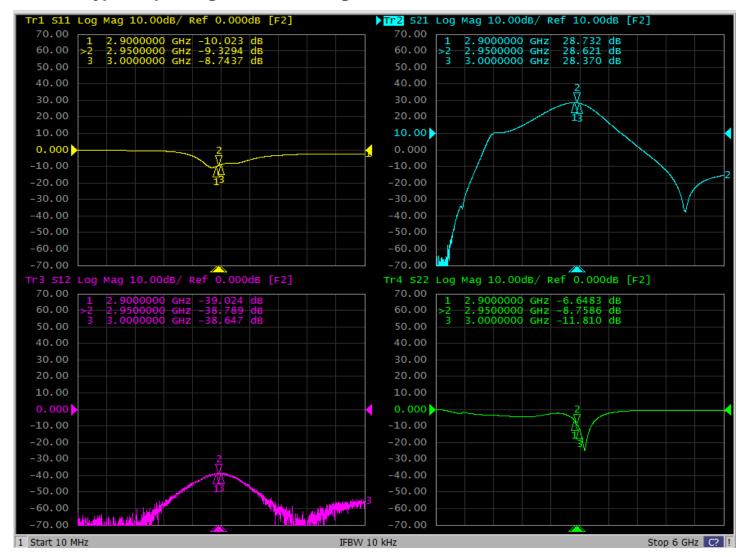
### **GRF5529 Typical Operating Curves: 2.95 GHz Tune**





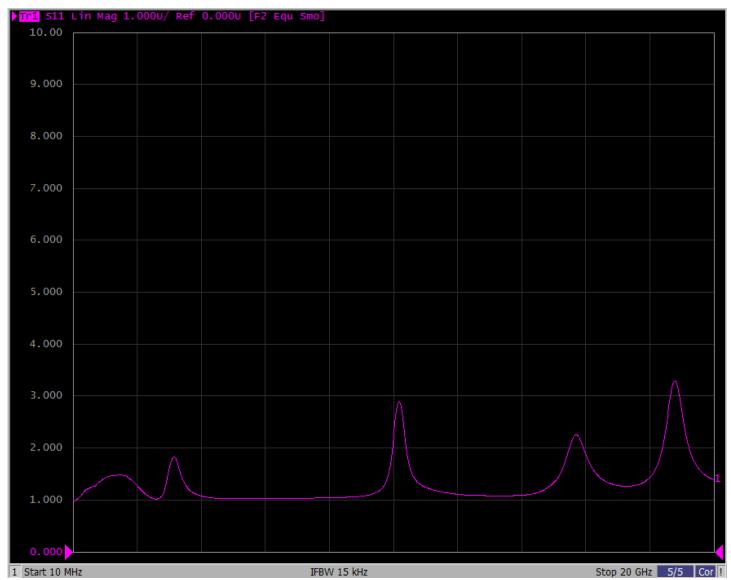


### **GRF5529 Typical Operating Curves: Small Signal S-Parameters (2.9 to 3.0 GHz Tune)**





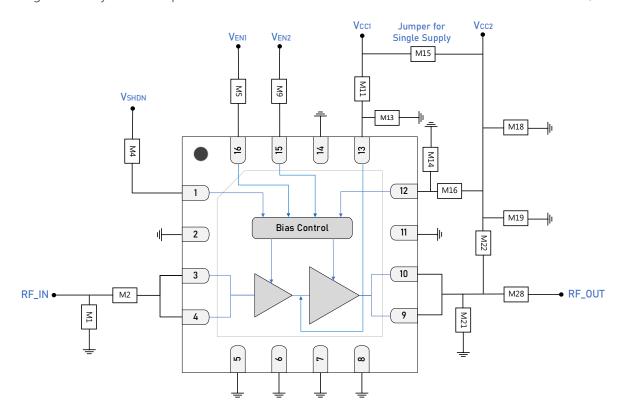
### GRF5529 Typical Operating Curves: Stability Mu - Small Signal (10 MHz to 20 GHz)



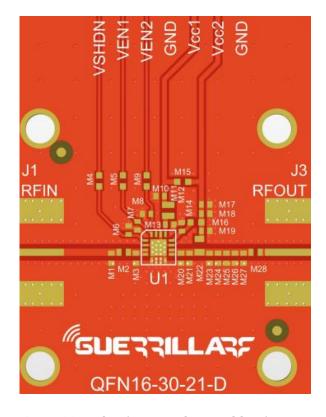
Note: Mu factor ≥ 1.0 implies unconditional stability.



#### **GRF5529** High Efficiency Power Amplifier 2.95 GHz



**GRF5529 Standard Evaluation Board Schematic** 



**GRF5529 Evaluation Board Assembly Diagram** 

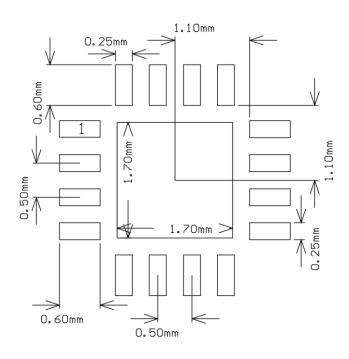


### **GRF5529 Evaluation Board Assembly Diagram Reference: 2.95 GHz Tune**

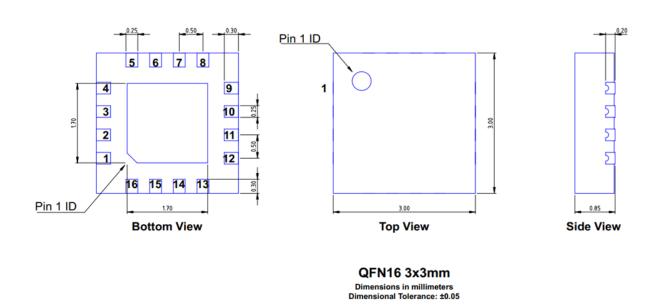
Component	Туре	Manufacturer	Family	Value	Package Size	Substitution
M1	Inductor	Murata	LQP	1.5 nH	0402	ok
M2	Capacitor	Murata	GJM	1.0 pF	0402	ok
M4	Resistor	Various		0 Ω	0402	ok
M5	Resistor	Various	5%	6.65 kΩ	0402	ok
M9	Resistor	Various	5%	4.75 kΩ	0402	ok
M11	Resistor	Various		0 Ω	0402	ok
M13	Capacitor	Murata	GRM	0.1 μF	0402	ok
M14	Capacitor	Murata	GRM	10 μF	0402	ok
M15	Resistor (Jumper)	Various		0 Ω	0402	ok
M16	Resistor	Various		0 Ω	0402	ok
M18	Capacitor	Murata	GRM	10 μF	0402	ok
M19	Capacitor	Murata	GRM	100 pF	0402	ok
M21	Capacitor	Murata	GJM	2.2 pF	0402	ok
M22	Inductor: High-Q	Murata	LQW	3.9 nH	0603	ok
M28	Capacitor	Murata	GJM	10 pF	0402	ok
Evaluation Board	QFN16-30-21-D					

Note: Standard evaluation board bias:  $V_{CC} = 5 \text{ V}$ ,  $V_{ENABLE} = 5 \text{ V}$ .





3 x 3 mm QFN-16 Suggested PCB Footprint (Top View)



3 x 3 mm QFN-16 Package Dimensions



### **Package Marking Diagram**



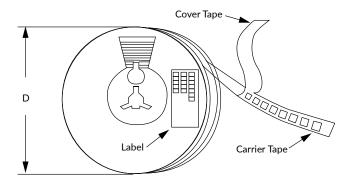
- Line 1: "YY" = YEAR. "WW" = WORK WEEK the device was assembled.
- Line 2: "GRF" = Guerrilla RF.
- Line 3: "XXXX" = Device PART NUMBER.

### **Tape and Reel Information**

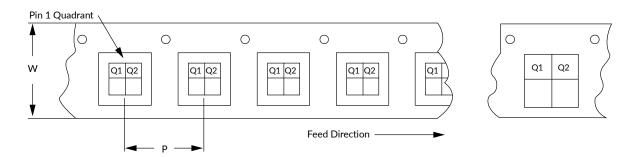
Guerrilla RF's tape and reel specification complies with Electronic Industries Alliance (EIA) standards for "Embossed Carrier Tape of Surface Mount Components for Automatic Handling" (reference EIA-481). See the following page for the Tape and Reel Specification and Device Package Information table, which includes units per reel.

Devices are loaded with pins down into the carrier pocket with protective cover tape and reeled onto a plastic reel. Each reel is packaged in a cardboard box. There are product labels on the reel, the protective ESD bag and the outside surface of the box.

For the Tape and Reel Reference Table, please refer to: https://www.querrilla-rf.com/prodFiles/Manufacturing/MN001.pdf



Tape and Reel Packaging with Reel Diameter Noted (D)



Carrier Tape Width (W), Pitch (P), Feed Direction and Pin 1 Quadrant Information



### **GRF5529** High Efficiency Power Amplifier 2.95 GHz

### **Revision History**

Revision Date	Description of Change
December 13, 2021	Preliminary Data Sheet.
March 8, 2022	Updated Package Marking Diagram.
May 10, 2022	Changed HBM Minimum Specification from TBD to 1500 V.
January 23, 2023	Added Characterization Plots. In the Absolute Ratings Table: Added the following condition to Maximum Dissipated Power for Stage-1 & 2: DC only. No RF applied. Changed Maximum Dissipated Power Stage-2 specification from 1400 to 850 mW.
September 20, 2024	Release Ø Data Sheet. Updated specifications. Added new Spar & Mu Plots.
January 17, 2025	Updated Data Sheet with minor cosmetic changes only. No change to device or device specifications.







#### **Datasheet Classifications**

Data Sheet Status	Notes
Advance	S-parameter and NF data based on EM simulations for the fully packaged device using foundry-supplied transistor S-parameters. Linearity estimates based on device size, bias condition and experience with related devices.
Preliminary	All data based on limited evaluation board measurements taken within the Guerrilla RF Applications Lab. All parametric values are subject to change pending the collection of additional data.
Release Ø	All data based on measurements taken with <i>production-released</i> material. TYP values are based on a combination of ATE and bench-level measurements, with MIN/MAX limits defined using <i>modelled estimates</i> that account for part-to-part variations and expected process spreads. Although unlikely, future refinements to the TYP/MIN/MAX values may be in order as multiple lots are processed through the factory.
Release A-Z	All data based on measurements taken with production-released material derived from multiple lots which have been fabricated over an extended period of time. MIN/MAX limits may be refined over previous releases as more statistically significant data is collected to account for process spreads.

Information in this datasheet is specific to the Guerrilla RF, Inc. ("Guerrilla RF") product identified.

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